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(71) Applicant (for all designated States except US): **THE REGENTS OF THE UNIVERSITY OF CALIFORNIA** [US/US]; 1111 Franklin Street, 12th Floor, Oakland, CA 94607-5200 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **MAJUMDAR, Arun** [US/US]; 151 Ardith Drive, Orinda, CA 94563 (US). **SHAKOURI, Ali** [IR/US]; 246 Dickens Way, Santa Cruz, CA 95064 (US). **SANDS, Timothy, D.** [US/US]; 1712 Del Monte Way, Berkeley, CA 94705 (US). **YANG, Peidong** [CN/US]; 3001 Derby Street, #F, Berkeley, CA 94705 (US). **MAO, Samuel, S.** [CN/US]; 7325 Lamar Loop, Castro Valley, CA 94552 (US). **RUSO, Richard, E.** [US/US]; 123 Crosby Court, #3, Walnut Creek, CA 94598 (US). **FEICK, Henning** [DE/US]; 37 Kerr Avenue, Kensington, CA 94707 (US). **KIND, Hannes** [CH/CH]; Steigstrasse 94, CH-8200 Schaffhausen (CH). **WEBER,**

Eicke, R. [US/US]; 6995 Elverton Drive, Oakland, CA 94611 (US). **HUANG, Michael** [US/US]; 11120 Queensland Street, H53, Los Angeles, CA 90034 (US). **YAN, Haoquan** [CN/US]; 257 Wilson Street, Albany, CA 94710 (US). **WU, Yiyang** [CN/US]; 257 Wilson Street, Albany, CA 94710 (US). **FAN, Rong** [US/US]; 5550 Central Avenue, #7, El Cerrito, CA 94530 (US).

(74) Agent: **O'BANION, John, P.**; O'Banion & Ritchey LLP, Suite 1550, 400 Capitol Mall, Sacramento, CA 95814 (US).

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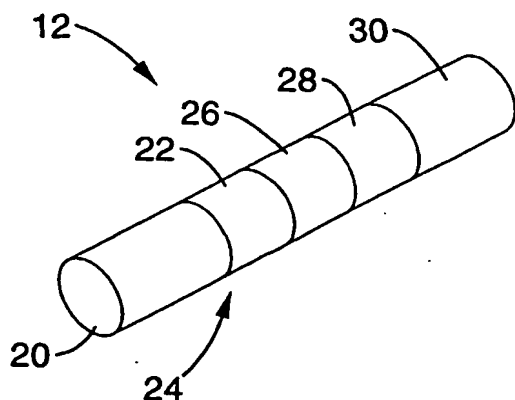
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(54) Title: METHODS OF FABRICATING NANOSTRUCTURES AND NANOWIRES AND DEVICES FABRICATED THEREFROM



(57) Abstract: One-dimensional nanostructures having uniform diameters of less than approximately 200 nm. These inventive nanostructures, which we refer to as "nanowires", include single-crystalline homostructures as well as heterostructures of at least two single-crystalline materials having different chemical compositions. Because single-crystalline materials are used to form the heterostructure, the resultant heterostructure will be single-crystalline as well. The nanowire heterostructures are generally based on a semiconducting wire wherein the doping and composition are controlled in either the longitudinal or radial directions, or in both directions, to yield a wire that comprises different materials. Examples of resulting nanowire heterostructures include a longitudinal heterostructure nanowire (LOHN) and a coaxial heterostructure nanowire (COHN).

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